## DATA SHEET

# SILICON POWER TRANSISTOR 2SD1481

### NPN SILICON EPITAXIAL TRANSISTOR (DARLINGTON CONNECTION) FOR LOW-FREQUENCY POWER AMPLIFIERS AND LOW-SPEED SWITCHING

#### FEATURES

NEC

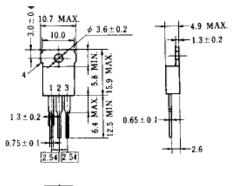
- On-chip C-to-B Zener diode for surge voltage absorption
- Low collector saturation voltage: VCE(SAT) = 1.5 V MAX. (at 1 A)
- Ideal for use in a direct drive from IC to the devices such as OA and FA equipment and motor solenoid relay printer head drivers

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vсво	60 ±10	V
Collector to emitter voltage	VCEO	60 ±10	V
Emitter to base voltage	Vebo	7.0	V
Collector current	IC(DC)	2.0	А
Collector current	IC(pulse)*	4.0	А
Base current	B(DC)	0.2	А
Total power dissipation	P⊤ (Tc = 25°C)	15	W
Total power dissipation	P⊤ (Ta = 25°C)	1.5	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

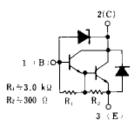
#### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

#### \* PW $\leq$ 300 $\mu$ s, duty cycle $\leq$ 10%

#### PACKAGE DRAWING (UNIT: mm)







Electrode Connection

- 1. Base
- Collector
   Emitter
- 4. Fin (collector)

#### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

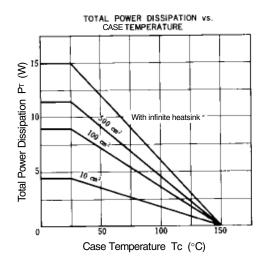
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = 40 V, I_E = 0$			1.0	μA
DC current gain	h <sub>FE1</sub>	Vce = 2.0 V, Ic = 1.0 A*	2,000		20,000	
DC current gain	hFE2	Vce = 2.0 V, Ic = 3.0 A*	500			
Collector saturation voltage	VCE(sat)	Ic = 1.0 A, Iв = 1.0 mA*			1.5	V
Base saturation voltage	VBE(sat)	Ic = 1.0 A, Iв = 1.0 mA*			2.0	V
Turn-on time	ton	Ic = 1.0 A, I <sub>B1</sub> = $-I_{B2}$ = 10 mA R <sub>L</sub> = 50 $\Omega$ , Vcc $\cong$ 50 V Refer to the test circuit.		0.5		μs
Storage time	tstg			2.0		μs
Fall time	tr			1.0		μs

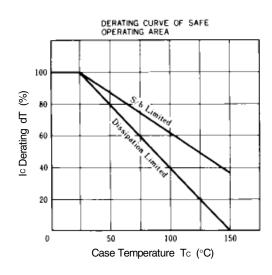
\* Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2%

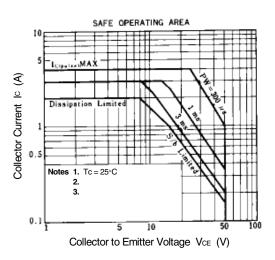
#### **hfe CLASSIFICATION**

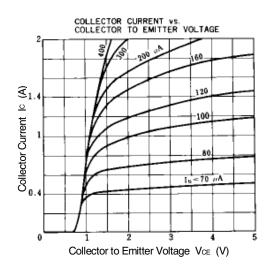
Marking	М	L	к
hfe1	2,000 to 5,000	4,000 to 10,000	8,000 to 20,000

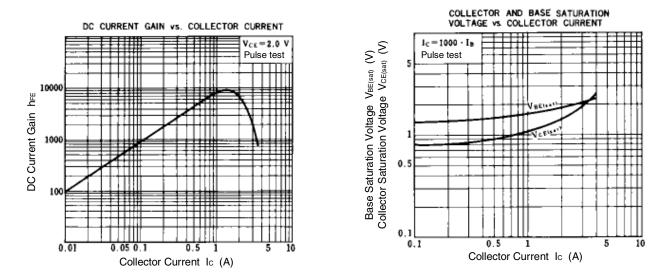
#### **TYPICAL CHARACTERISTICS (Ta = 25°C)**



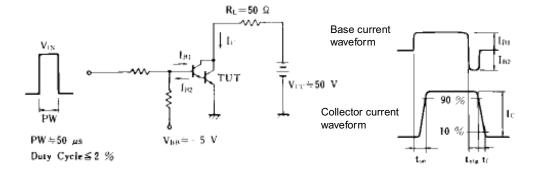








SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT



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